# **Low Power Transistors**

### **NPN Silicon**

#### **Features**

- MIL-PRF-19500/391 Qualified
- Available as JAN, JANTX, and JANTXV

#### **MAXIMUM RATINGS** (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol                            | Value          | Unit |
|---|-----------------------------------|----------------|------|
| Collector - Emitter Voltage   | V <sub>CEO</sub>                  | 80             | Vdc  |
| Collector - Base Voltage  | V <sub>CBO</sub>                  | 140            | Vdc  |
| Emitter - Base Voltage  | V <sub>EBO</sub>                  | 7.0            | Vdc  |
| Collector Current – Continuous  | I <sub>C</sub>                    | 1.0            | Adc  |
| Total Device Dissipation @ T <sub>A</sub> = 25°C<br>2N3019, 2N3019S<br>2N3700 | P <sub>T</sub>                    | 800<br>500     | mW   |
| Total Device Dissipation @ T <sub>C</sub> = 25°C<br>2N3019, 2N3019S<br>2N3700 | P <sub>T</sub>                    | 5.0<br>1.0     | W    |
| Operating and Storage Junction<br>Temperature Range                           | T <sub>J</sub> , T <sub>stg</sub> | -65 to<br>+200 | °C   |

#### THERMAL CHARACTERISTICS

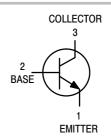
| Characteristic   | Symbol         | Max        | Unit |
|--|----------------|------------|------|
| Thermal Resistance, Junction to Ambient 2N3019, 2N3019S 2N3700 | $R_{	hetaJA}$  | 195<br>325 | °C/W |
| Thermal Resistance, Junction to Case 2N3019, 2N3019S 2N3700    | $R_{	heta JC}$ | 30<br>150  | °C/W |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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TO-39 CASE 205AB STYLE 1 2N3019S



TO-18 CASE 206AA STYLE 1 2N3700

#### **ORDERING INFORMATION**

| Device        | Package | Shipping |
|---------------|---------|----------|
| JAN2N3019     |         |          |
| JANTX2N3019   | TO-5    | Bulk     |
| JANTXV2N3019  |         |          |
| JAN2N3019S    |         |          |
| JANTX2N3019S  | TO-39   | Bulk     |
| JANTXV2N3019S |         |          |
| JAN2N3700     |         |          |
| JANTX2N3700   | TO-18   | Bulk     |
| JANTXV2N3700  |         |          |

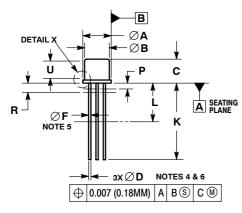
## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

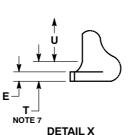
| Characteristic  | Symbol                             | Min                         | Max                         | Unit         |
|---|------------------------------------|-----------------------------|-----------------------------|--------------|
| OFF CHARACTERISTICS   | <u> </u>                           | 1                           | 1                           | ı            |
| Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 30 mAdc)  | V <sub>(BR)CEO</sub>               | 80                          | _                           | Vdc          |
| Emitter-Base Cutoff Current<br>(V <sub>EB</sub> = 5.0 Vdc)<br>(V <sub>EB</sub> = 7.0 Vdc)   | I <sub>EBO</sub>                   | -<br>-                      | 10<br>10                    | nAdc<br>μAdc |
| Collector–Emitter Cutoff Current (V <sub>CE</sub> = 90 Vdc)   | I <sub>CEO</sub>                   | -                           | 10                          | nAdc         |
| Collector–Base Cutoff Current (V <sub>CB</sub> = 140 Vdc)   | I <sub>CBO</sub>                   | -                           | 10                          | μAdc         |
| ON CHARACTERISTICS (Note 1)   | 1                                  |                             |                             | l .          |
| DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=500 \text{ mAdc, } V_{CE}=10 \text{ Vdc)} \\ (I_C=1.0 \text{ Adc, } V_{CE}=10 \text{ Vdc)} \end{array} $ | h <sub>FE</sub>                    | 50<br>90<br>100<br>50<br>15 | 300<br>-<br>300<br>300<br>- | -            |
| Collector – Emitter Saturation Voltage ( $I_C$ = 150 mAdc, $I_B$ = 15 mAdc) ( $I_C$ = 500 mAdc, $I_B$ = 50 mAdc)  | V <sub>CE(sat)</sub>               | -<br>-                      | 0.2<br>0.5                  | Vdc          |
| Base – Emitter Saturation Voltage<br>(I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)  | V <sub>BE(sat)</sub>               | -                           | 1.1                         | Vdc          |
| SMALL-SIGNAL CHARACTERISTICS  | <u> </u>                           |                             | •                           |              |
| Magnitude of Small–Signal Current Gain (I <sub>C</sub> = 50 mAdc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)   | h <sub>fe</sub>                    | 5.0                         | 20                          | -            |
| Small–Signal Current Gain ( $I_C = 1.0$ mAdc, $V_{CE} = 5$ Vdc, $f = 1$ kHz)  | h <sub>fe</sub>                    | 80                          | 400                         | -            |
| Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz})$  | C <sub>obo</sub>                   | -                           | 12                          | pF           |
| Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$ )  | C <sub>ibo</sub>                   | -                           | 60                          | pF           |
| Noise Figure ( $V_{CE}$ = 10 Vdc, $I_{C}$ = 100 $\mu$ Adc, $R_{g}$ = 1 $k\Omega$ , PBW = 200 Hz)  | NF                                 | -                           | 4.0                         | dB           |
| Collector–Base Time Constant<br>(V <sub>CB</sub> = 10 Vdc, I <sub>C</sub> = 10 mAdc, f = 79.8 MHz)  | r' <sub>b</sub> ,C <sub>C</sub>    | -                           | 400                         | ps           |
| SWITCHING CHARACTERISTICS   | -                                  | •                           | •                           | •            |
| Pulse Response<br>(Reference Figure in MIL-PRF-19500/391)   | t <sub>on</sub> + t <sub>off</sub> | -                           | 30                          | ns           |
| SWITCHING CHARACTERISTICS Pulse Response  | t <sub>on</sub> + t <sub>off</sub> | _                           |                             | ns           |

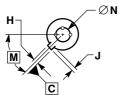
<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

#### **PACKAGE DIMENSIONS**

TO-53-Lead CASE 205AA **ISSUE B** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
- CONTROLLING DIMENSION: INCHES.
   DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
- LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
- DIMENSION F APPLIES BETWEEN DIMENSION P AND L
  DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
  BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-
- SIONS A, B, AND T.

  8. DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

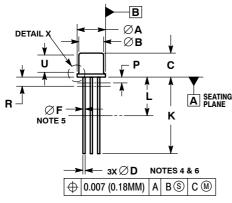
|     | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
| DIM | MIN         | MAX   | MIN       | MAX   |
| Α   | 8.89        | 9.40  | 0.350     | 0.370 |
| В   | 8.00        | 8.51  | 0.315     | 0.335 |
| С   | 6.10        | 6.60  | 0.240     | 0.260 |
| D   | 0.41        | 0.53  | 0.016     | 0.021 |
| E   | 0.23        | 3.18  | 0.009     | 0.125 |
| F   | 0.41        | 0.48  | 0.016     | 0.019 |
| Н   | 0.71        | 0.86  | 0.028     | 0.034 |
| J   | 0.73        | 1.02  | 0.029     | 0.040 |
| K   | 38.10       | 44.45 | 1.500     | 1.750 |
| L   | 6.35        |       | 0.250     |       |
| M   | 45°BSC      |       | 45 °BSC   |       |
| N   | 5.08 BSC    |       | 0.200 BSC |       |
| P   |             | 1.27  |           | 0.050 |
| R   | 1.37 BSC    |       | 0.054 BSC |       |
| T   |             | 0.76  |           | 0.030 |
| U   | 2.54        |       | 0.100     |       |

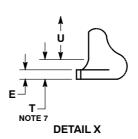
#### STYLE 1:

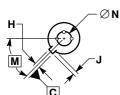
PIN 1. EMITTER

- BASE
- COLLECTOR

#### TO-39 3-Lead CASE 205AB **ISSUE A**









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE. LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE
- PLANE DEFINED BY DIMENSION R.
  DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
- DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
  BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-
- SIONS A, B, AND T.
  DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

| DINIENSION D SHALL NOT VART WORL TH |             |          |        |           |  |
|-------------------------------------|-------------|----------|--------|-----------|--|
|                                     | MILLIMETERS |          | INCHES |           |  |
| DIM                                 | MIN         | MAX      | MIN    | MAX       |  |
| Α                                   | 8.89        | 9.40     | 0.350  | 0.370     |  |
| В                                   | 8.00        | 8.51     | 0.315  | 0.335     |  |
| С                                   | 6.10        | 6.60     | 0.240  | 0.260     |  |
| D                                   | 0.41        | 0.48     | 0.016  | 0.019     |  |
| E                                   | 0.23        | 3.18     | 0.009  | 0.125     |  |
| F                                   | 0.41        | 0.48     | 0.016  | 0.019     |  |
| Н                                   | 0.71        | 0.86     | 0.028  | 0.034     |  |
| J                                   | 0.73        | 1.02     | 0.029  | 0.040     |  |
| K                                   | 12.70       | 14.73    | 0.500  | 0.580     |  |
| L                                   | 6.35        |          | 0.250  |           |  |
| M                                   | 45°         | 45 °BSC  |        | BSC       |  |
| N                                   | 5.08        | BSC      | 0.200  | BSC       |  |
| P                                   |             | 1.27     |        | 0.050     |  |
| R                                   | 1.37        | 1.37 BSC |        | 0.054 BSC |  |
| T                                   |             | 0.76     |        | 0.030     |  |
| U                                   | 2.54        |          | 0.100  |           |  |

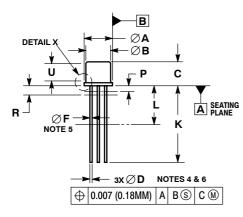
#### STYLE 1:

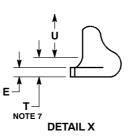
EMITTER PIN 1.

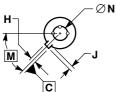
BASE COLLECTOR 3.

#### PACKAGE DIMENSIONS

TO-18 3-Lead CASE 206AA **ISSUE A** 









DETAIL

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: INCHES.
- CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
  LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE
- PLANE DEFINED BY DIMENSION R.
  DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
- DIMENSION D APPLIES BETWEEN DIMENSION L AND K. BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-
- SIONS A, B, AND T.

|     | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
| DIM | MIN         | MAX   | MIN       | MAX   |
| Α   | 5.31        | 5.84  | 0.209     | 0.230 |
| В   | 4.52        | 4.95  | 0.178     | 0.195 |
| С   | 4.32        | 5.33  | 0.170     | 0.210 |
| D   | 0.41        | 0.53  | 0.016     | 0.021 |
| Е   |             | 0.76  |           | 0.030 |
| F   | 0.41        | 0.48  | 0.016     | 0.019 |
| Н   | 0.91        | 1.17  | 0.036     | 0.046 |
| J   | 0.71        | 1.22  | 0.028     | 0.048 |
| K   | 12.70       | 19.05 | 0.500     | 0.750 |
| L   | 6.35        |       | 0.250     |       |
| M   | 45°BSC      |       | 45 °BSC   |       |
| N   | 2.54        | BSC   | 0.100 BSC |       |
| Р   |             | 1.27  |           | 0.050 |
| R   | 1.37 BSC    |       | 0.054 BSC |       |
| T   |             | 0.76  |           | 0.030 |
| U   | 2.54        |       | 0.100     |       |

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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